

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Docket No: Q77903

Arie GLAZER, et al.

Appln. No.: 10/694,392

Group Art Unit: 1765

Confirmation No.: 9177

Examiner: Anita Karen ALANKO

Filed: October 28, 2003

For: SELECTABLE AREA LASER ASSISTED PROCESSING OF SUBSTRATES

RESPONSE TO NOTICE OF NON-COMPLIANT AMENDMENT

MAIL STOP AMENDMENT

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

Sir:

In response to the Notice of Non-Compliant Amendment dated July 19, 2006, please enter and consider the following

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AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

Claims 1. – 55. (canceled)

56. (currently amended): A method of fabricating thin film transistors, comprising:
| forming at least one semi-conductive film on a substrate;
| immersing said substrate in a dopant; and
| delivering a laser beam to a plurality of independently selectable locations on said
| substrate with a plurality of independently tiltable beam steering elements to induce a doping
| reaction between said dopant and said semi-conductive film at said independently selectable
| locations.

57. (currently amended): The method claimed in claim 56, wherein said semi-conductive film
comprises a semiconductor film..

58. (currently amended): The method claimed in claim 56, wherein said semi-conductive film
comprises silicon.

59. (currently amended): The method claimed in claim 58, wherein said semi-conductive film
is deposited on an insulating substrate.

60. (original): The method claimed in claim 59 and wherein said insulating substrate
comprises glass.

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61. (currently amended): The method claimed in claim 56, wherein said locations correspond to locations whereat transistors are to be formed in said semi-conductive film.

62. (original): The method claimed in claim 56, wherein said immersing said substrate comprises showering ionized molecules onto said substrate.

63. (original): The method claimed in claim 56, wherein said delivering a laser beam comprises splitting a first laser beam into a plurality of sub-beams, and delivering said sub-beams to mutually independently selectable locations.

64. (canceled)

65. (original): The method claimed in claim 64, wherein said delivering a laser beam further comprises modulating said laser beam to deliver said pulses exclusively to said selected locations.

66. (original): The method claimed in claim 56, wherein said delivering a laser beam comprises delivering said laser beam to said selectable locations that are at least partially isolated from other said selectable locations.

67. (original): The method claimed in claim 56, wherein said delivering comprises delivering said laser beam to said selectable locations that vary from other said selectable locations in size.

68. (original): The method claimed in claim 56, wherein said delivering comprises delivering said laser beam to said selectable locations that vary from other said selectable locations in spacing.

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69. (original): The method claimed in claim 56, wherein said delivering a laser beam comprises modulating an energy characteristic of said laser beam.

70. (original): The method claimed in claim 69, wherein said delivering a laser beam comprises delivering said laser beam with a first modulated energy characteristic to a first independently selectable location, and then delivering said laser beam with a second modulated energy characteristic to a second independently selectable location.

71. (original): The method claimed in claim 56, wherein said delivering a laser beam comprises delivering a pulsed laser beam having a pulse repetition rate of greater than 5 KHz.

72. (original): The method claimed in claim 56, further comprising individually heating each of said selectable locations to at least partially melt said conductive film thereat.

73. (original): The method claimed in claim 56, wherein said delivering a laser beam comprises selecting locations during operation of a laser supplying said laser beam.

74. (currently amended): The method claimed in claim 56, wherein said delivering a laser beam comprises selecting locations during performing a doping reaction induction operation on said conductive film.

75. (original): The method claimed in claim 73, wherein said selecting comprises steering said laser beam to said selectable locations.

76. (canceled)

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77. (original): The method claimed in claim 56, wherein said delivering a laser beam comprises delivering said laser beam to said independently selectable locations without an intervening photo mask.

78. (original): The method claimed in claim 77, wherein said delivering a laser beam comprises selecting said independently selectable locations during operation of a laser supplying said laser beam.

Claims 79. – 110. (canceled)

111. (currently amended): A method of producing thin film transistors on a substrate, comprising:

generating a laser beam;
splitting said laser beam into a plurality of selectively positionable sub-beams; and
directing each of said sub-beams to selectable areas on said substrate with an
independently tiltable beam steering element, said selectable areas corresponding to locations
whereat said transistors are to be formed, in the presence of a doping gas to induce a doping
reaction between said substrate and said doping gas at said selectable areas.

112. (original): The method according to claim 111, wherein each of said selectable areas is at least partially isolated from another one of said selectable areas.

113. (original): The method according to claim 111, wherein at least one of said selectable areas vary from each other in size and spacing.

114. (original): The method according to claim 111, wherein said laser beam is a pulsed laser beam having a pulse repetition rate of greater than 5 KHz.

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115. (original): The method according to claim 111, wherein said sub-beams are independently guided so as to interact with said doping gas and with said substrate surface, at each of said selectable areas.

116. (original): The method according to claim 111, further comprising individually heating each of said selectable areas thereby forming bases of said transistors.

Claims 117 – 125. (canceled)

126. (currently amended): A method of manufacturing an array of thin film transistors, comprising:

depositing amorphous silicon on a substrate;

crystallizing said amorphous silicon by applying laser energy to said amorphous silicon at a plurality of selectable locations;

applying P type doping to portions of crystallized silicon by delivering laser energy to a plurality of selectable locations in presence of a P type doping agent;—;

wherein said plurality of selectable locations are selected using a plurality of independently tiltable beam steering elements

127. (original): The method claimed in claim 126, wherein said applying P type doping comprises forming PMOS channels.

128. (original): The method claimed in claim 126, further comprising: applying N type doping to portions of crystallized silicon by delivering laser energy to said plurality of selectable locations in presence of an N type doping agent.

129. (original): The method claimed in claim 128, wherein said applying N type doping comprises forming NMOS channels.

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130. (original): The method claimed in claim 127, further comprising:
applying N type doping to portions of crystallized silicon by delivering laser energy to
said plurality of selectable locations in presence of an N type doping agent.
131. (original): The method claimed in claim 130, wherein said applying N type doping
comprises forming NMOS channels.
132. (original): The method claimed in claim 131, further comprising forming dielectric gates.
133. (original): The method claimed in claim 131, further comprising: laser treating
crystallized silicon at said selectable locations to hydrogenate said selectable locations.
134. (original): The method claimed in claim 132, further comprising:
laser treating said selectable locations in said crystallized silicon in the presence of said P
doping agent to form PMOS type source/drains.
135. (original): The method claimed in claim 134, further comprising: laser treating selected
areas in said crystallized silicon in the presence of said N doping agent to form NMOS type
source/drains.
136. (original): The method claimed in claim 126, wherein at least one of dehydrogenating,
crystallizing said silicon, doping and hydrogenating is performed without masking.

Claim 137. (canceled)

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REMARKS

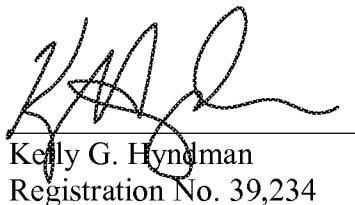
In response to the Notice of Non-Compliant Amendment, dated July 19, 2006, Applicant has amended the claim identifier's for the claims.

As instructed in the Notice of Non-Compliant Amendment, this Response contains only that portion of the July 7, 2006 Amendment that was indicated as being in non-compliance.

In view of the above, reconsideration and allowance of this application are now believed to be in order, and such actions are hereby solicited. If any points remain in issue which the Examiner feels may be best resolved through a personal or telephone interview, the Examiner is kindly requested to contact the undersigned at the telephone number listed below.

The USPTO is directed and authorized to charge all required fees, except for the Issue Fee and the Publication Fee, to Deposit Account No. 19-4880. Please also credit any overpayments to said Deposit Account.

Respectfully submitted,



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